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INFORMATION DISCLOSURE
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APPLICATION NO.	N/A
FILING DATE	Herewith
FIRST NAMED INVENTOR	David T. Beatson
ART UNIT	N/A
EXAMINER NAME	N/A
ATTORNEY DOCKET NO.	P26229-A USA

U.S. PATENT DOCUMENTS



EXAMINER INITIALS		DOCUMENT NO.	PUBLICATION DATE	NAME
JS	AA	6,885,104	April 26, 2005	Ellis , et al.
JS	AB	6,599,561	July 29, 2003	Dow , et al.
JS	AC	6,534,877	March 18, 2003	Ellis , et al.
JS	AD	6,413,576	July 2, 2002	Ellis , et al.
JS	AE	6,352,743	March 5, 2002	Ellis , et al.
JS	AF	6,156,990	December 5, 2000	Ellis
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FOREIGN PATENT DOCUMENTS

EXAMINER INITIALS		DOCUMENT NO.	PUBLICATION DATE	COUNTRY
JS	BA	WO 01/01478 A	January 4, 2001	PCT
JS	BB	PCT/US2004/087150 A1	May 6, 2004	PCT
JS	BC	PCT/ US2004/155702 A 1	October 24, 2002	PCT
JS	BD	PCT/US2002/168845 A1	November 14, 2002	PCT
JS	BE	WO 01/01478 A	April 01, 2001	PCT
JS	BF	PCT/US2004/087150	June 5, 2004	PCT
JS	BG	PCT/US2002/155702 A1	October 10, 2002	PCT
JS	BH	PCT/US/2002/168845 A1	November 11, 2002	PCT
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OTHER PUBLICATIONS

	CA	Noguchi J. et al: "Effect of NH3-Plasma Treatment and CMP Modification on TDDDB Improvement in U Metallization", IEEE Transaction on Electron Devices, vol. 48, no. 7, IEEE Inc. NY, US, July 2001.
	CB	Maruyama T.; Morishita T. "Copper Nitride Thin Films Prepared by Radio Frequency Reactive Sputtering" J. Appl. Physics, vol. 78, no. 6, September 1995.
	CC	

James Sells
EXAMINER

2-5-07
DATE CONSIDERED

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformation and not considered. Include copy of this form with next communication to applicant.